

ABSTRACT OF THE DISCLOSURE

There is provided a new method of obtaining the dopant activation rate of a device accurately and simply in a different way from a method of obtaining a carrier density with use of a Hall measurement or CV measurement, and also provided a production method of a device performed with a proper threshold voltage control, that is, a dose amount control, according to the obtained activation rate. The inventor devised a method in which the activated dopant density (first dopant density) in a semiconductor film is obtained from the threshold voltage and the flat band voltage of a device, then the dopant activation rate is obtained from the ratio of the obtained activated dopant density to the added dopant density (second dopant density) obtained by SIMS analysis. The invention allows easily obtaining the dopant activation rate in the channel region and the impurity region of the device.